

CD4041UBMS

Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) -0.5V to +20V
 (Voltage Referenced to VSS Terminals)
 Input Voltage Range, All Inputs -0.5V to VDD +0.5V
 DC Input Current, Any One Input. ±10mA
 Operating Temperature Range -55°C to +125°C
 Package Types D, F, K, H
 Storage Temperature Range (TSTG). -65°C to +150°C
 Lead Temperature (During Soldering) +265°C
 At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for
 10s Maximum

Reliability Information

Thermal Resistance. θ_{ja} θ_{jc}
 Ceramic DIP and FRIT Package 80°C/W 20°C/W
 Flatpack Package. 70°C/W 20°C/W
 Maximum Package Power Dissipation (PD) at +125°C
 For TA = -55°C to +100°C (Package Type D, F, K) 500mW
 For TA = +100°C to +125°C (Package Type D, F, K) Derate
 Linearity at 12mW/°C to 200mW
 Device Dissipation per Output Transistor. 100mW
 For TA = Full Package Temperature Range (All Package Types)
 Junction Temperature +175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
						MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	2	µA
				2	+125°C	-	200	µA
		VDD = 18V, VIN = VDD or GND		3	-55°C	-	2	µA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
			VDD = 18V	2	+125°C	-1000	-	nA
				3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
			VDD = 18V	2	+125°C	-	1000	nA
				3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	2.1	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	5.5	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	16.1	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-1.02	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-4.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	+25°C	-	-2.6	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	+25°C	-	-6.8	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA		1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA		1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	+25°C			
		VDD = 18V, VIN = VDD or GND		8A	+125°C			
		VDD = 3V, VIN = VDD or GND		8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	11	-	V
Tri-State Output Leakage	IOZL	VIN = VDD or GND VOUT = 0V	VDD = 20V	1	+25°C	-0.4	-	µA
			VDD = 18V	2	+125°C	-12	-	µA
				3	-55°C	-0.4	-	µA
Tri-State Output Leakage	IOZH	VIN = VDD or GND VOUT = VDD	VDD = 20V	1	+25°C	-	0.4	µA
			VDD = 18V	2	+125°C	-	12	µA
				3	-55°C	-	0.4	µA

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.
 2. Go/No Go test with limits applied to inputs.
 3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

CD4041UBMS

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay	TPHL	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	110	ns
			10, 11	+125°C, -55°C	-	149	ns
Propagation Delay	TPLH	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	150	ns
			10, 11	+125°C, -55°C	-	203	ns
Propagation Delay3 State	TPHZ TPZH	VDD = 5V, VIN = VDD or GND (Note 2, 3)	9	+25°C	-	140	ns
			10, 11	+125°C, -55°C	-	189	ns
Propagation Delay3 State	TPZL TPLZ	VDD = 5V, VIN = VDD or GND (Note 2, 3)	9	+25°C	-	180	ns
			10, 11	+125°C, -55°C	-	243	ns
Transition Time	TTHL	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	70	ns
			10, 11	+125°C, -55°C	-	95	ns
Transition Time	TTLH	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	90	ns
			10, 11	+125°C, -55°C	-	122	ns

NOTES:

1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.
3. CL = 50pF, RL = 1K, Input TR, TF < 20ns.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	1	μA
				+125°C	-	30	μA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μA
				+125°C	-	60	μA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μA
				+125°C	-	120	μA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	1.3	-	mA
				-55°C	2.6	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	3.8	-	mA
				-55°C	6.5	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	11.2	-	mA
				-55°C	19.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.7	mA
				-55°C	-	-1.2	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-3.0	mA
				-55°C	-	-5.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-1.8	mA
				-55°C	-	-3.1	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1, 2	+125°C	-	-4.8	mA
				-55°C	-	-8.2	mA

CD4041UBMS

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay	TPHL	VDD = 10V	1, 2, 3	+25°C	-	50	ns
		VDD = 15V	1, 2, 3	+25°C	-	35	ns
Propagation Delay	TPLH	VDD = 10V	1, 2, 3	+25°C	-	70	ns
		VDD = 15V	1, 2, 3	+25°C	-	50	ns
Propagation Delay	TPHZ TPZH	VDD = 10V	1, 2, 4	+25°C	-	60	ns
		VDD = 15V	1, 2, 4	+25°C	-	50	ns
Propagation Delay	TPZL TPLZ	VDD = 10V	1, 2, 4	+25°C	-	80	ns
		VDD = 15V	1, 2, 4	+25°C	-	70	ns
Transition Time	TTHL	VDD = 10V	1, 2, 3	+25°C	-	40	ns
		VDD = 15V	1, 2, 3	+25°C	-	25	ns
Transition Time	TTLH	VDD = 10V	1, 2, 3	+25°C	-	45	ns
		VDD = 15V	1, 2, 3	+25°C	-	35	ns
Input Capacitance	CIN	Any Inputs	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
4. CL = 50pF, RL = 1K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	7.5	μA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

- NOTES: 1. All voltages referenced to device GND. 2. CL = 50pF, RL = 200K, Input TR, TF < 20ns. 3. See Table 2 for +25°C limit. 4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-1	IDD	± 0.2μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

CD4041UBMS

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2, 3

NOTE: 1. 5% Parametric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± 0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 (Note 1)	3, 5, 7, 9, 11, 13	1, 2, 4, 6, 8, 10, 12, 14, 15	16			
Static Burn-In 2 (Note 1)	3, 5, 7, 9, 11, 13	8	1, 2, 4, 6, 10, 12, 14-16			
Dynamic Burn-In (Note 1)	-	1, 8, 15	16	3, 5, 7, 9, 11, 13	2, 4, 6, 10, 12, 14	
Irradiation (Note 2)	3, 5, 7, 9, 11, 13	8	1, 2, 4, 6, 10, 12, 14-16			

NOTES:

- Each pin except VDD and GND will have a series resistor of $10K \pm 5\%$, $VDD = 18V \pm 0.5V$
- Each pin except VDD and GND will have a series resistor of $47K \pm 5\%$; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, $VDD = 10V \pm 0.5V$

Logic Diagram

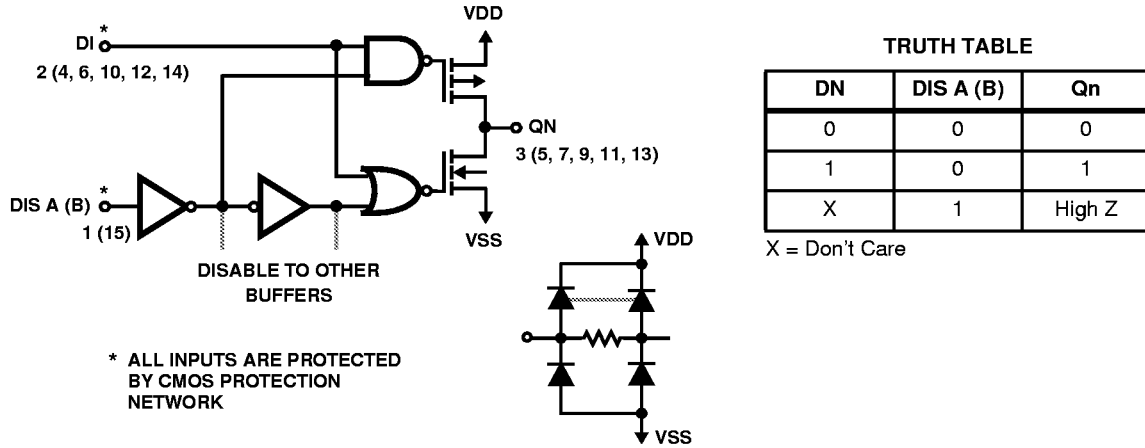


FIGURE 1. LOGIC DIAGRAM OF 1 TO 6 IDENTICAL BUFFERS

Typical Performance Characteristics

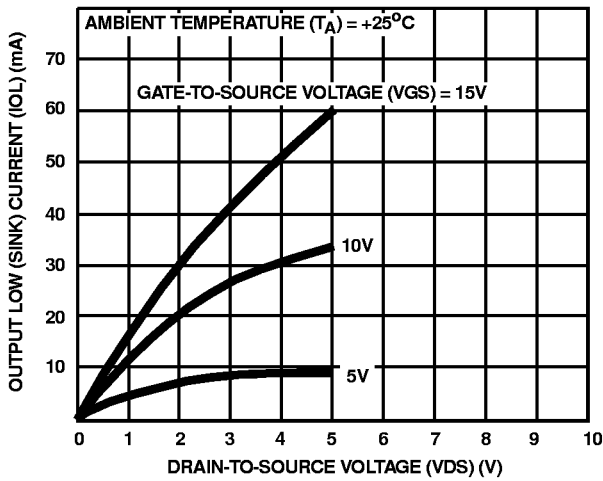


FIGURE 2. TYPICAL N-CHANNEL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

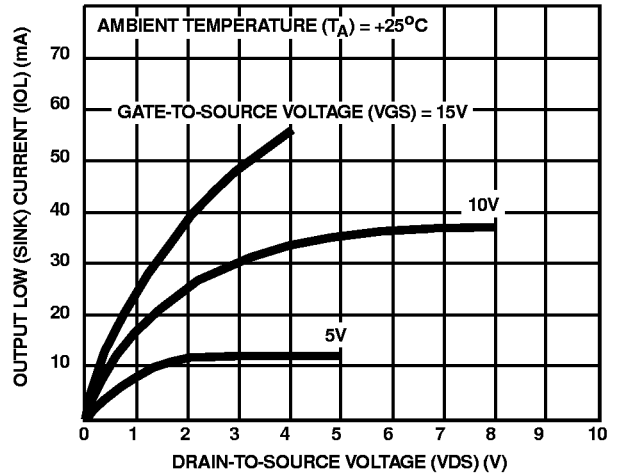


FIGURE 3. MINIMUM N-CHANNEL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

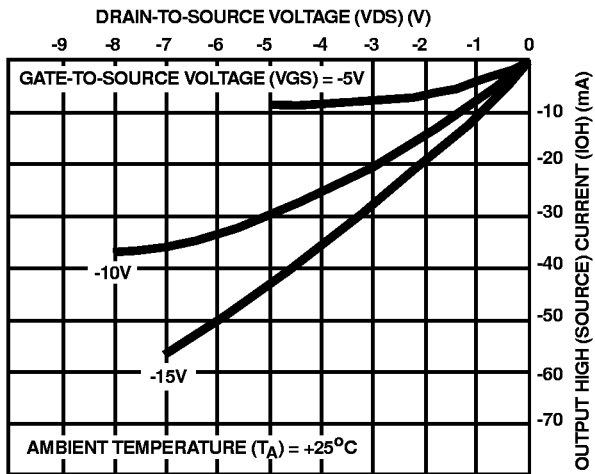


FIGURE 4. TYPICAL P-CHANNEL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

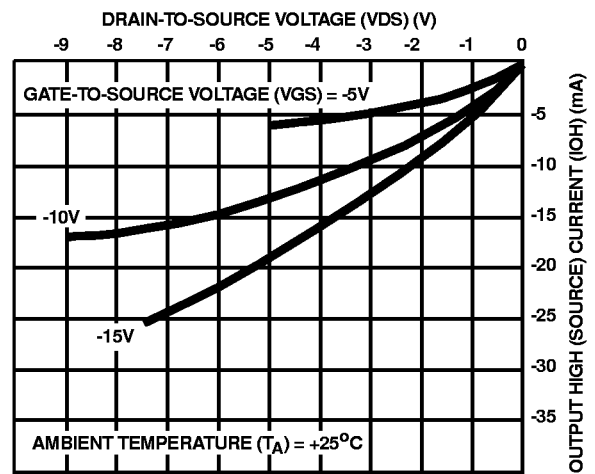


FIGURE 5. MINIMUM P-CHANNEL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

Typical Performance Characteristics (Continued)

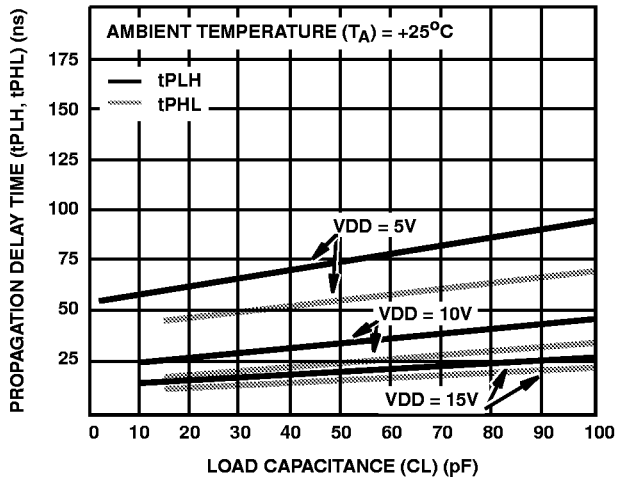


FIGURE 6. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE

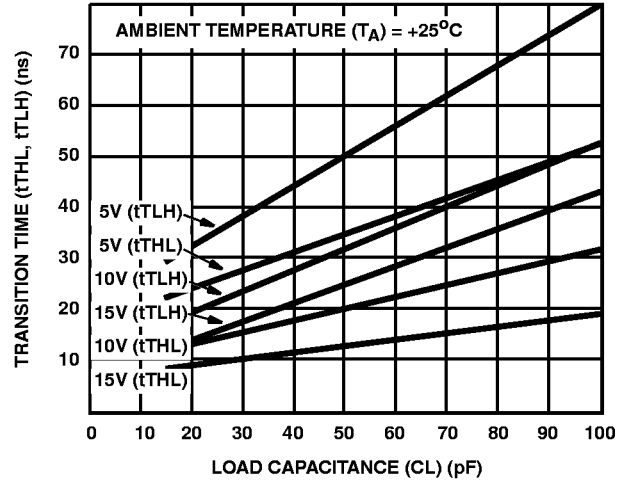


FIGURE 7. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

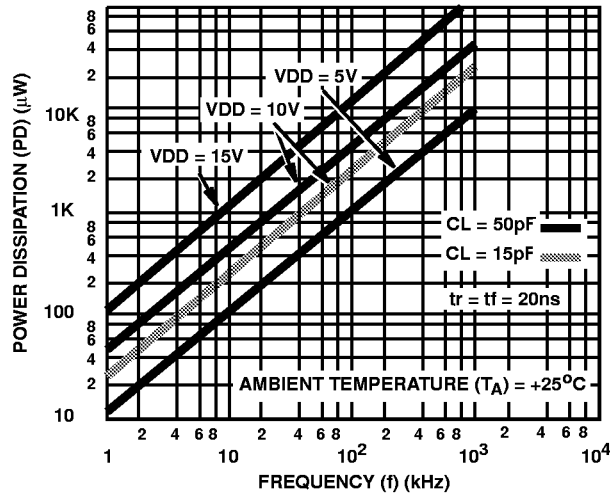
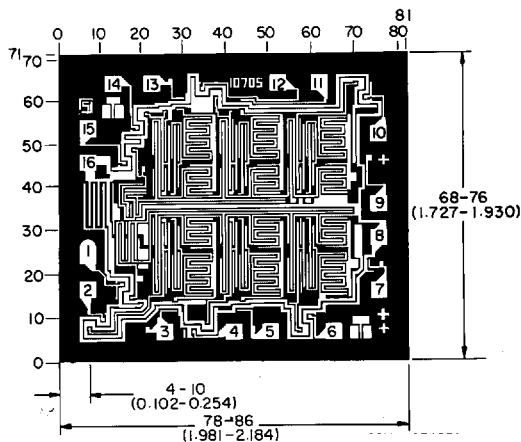


FIGURE 8. TYPICAL POWER DISSIPATION AS A FUNCTION OF FREQUENCY

Chip Dimensions and Pad Layout



Dimensions in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

- METALLIZATION:** Thickness: $11\text{k}\text{\AA} - 14\text{k}\text{\AA}$, AL.
- PASSIVATION:** $10.4\text{k}\text{\AA} - 15.6\text{k}\text{\AA}$, Silane
- BOND PADS:** 0.004 inches X 0.004 inches MIN
- DIE THICKNESS:** 0.0198 inches - 0.0218 inches